

Combustion synthesis of silicon carbide by magnesio-carbothermic reduction of amorphous and crystalline silica

Kirakosyan, Hasmik; Nazaretyan, Khachik; Beglaryan, Hayk; Ivanov, Roman; **Hussainova, Irina; Aydinyan, Sofiya** Proceedings of the Estonian Academy of Sciences 2025 / p. 260-265 <https://doi.org/10.3176/proc.2025.2.31>

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0,9 MeV electrons

Lebedev, Alexander A.; Davydovskaja, K. S.; Kozlovski, Vitali V.; **Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana** 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 49

Full SiC three-level T-type quasi-Z source inverter as grid-forming unit in islanded nanogrid

Gutiérrez-Escalona, Javier; Roncero Clemente, Carlos; **Matiushkin, Oleksandr; González Romera, Eva; Pires, V. Fernão; Romero Cadaval, Enrique** IET renewable power generation 2025 / art. e70051 <https://doi.org/10.1049/rpg2.70051>

Grid-frequency Vienna rectifier and isolated current-source DC-DC converters for efficient off-board charging of electric vehicles

Rabkowski, Jacek; **Blinov, Andrei; Zinchenko, Denys**; Wrona, Grzegorz; Zdanowski, Mariusz 2020 22nd European Conference on Power Electronics and Applications (EPE'20 ECCE Europe), Lyon, France, 7-11 Sept. 2020 / 10 p. : ill <https://doi.org/10.23919/EPE20ECCEurope43536.2020.9215772>

High-efficiency 312-kVA three-phase inverter using parallel connection of silicon carbide MOSFET power modules

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Nano- and Micro-Scale simulations of Ge/3C-SiC and Ge/4H-SiC NN-heterojunction diodes

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Numerical simulations of wideband SiC N-N heterostructure diode

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SEU study of wideband heterostructure diode for particle detection

Patankar, Udayan Sunil; Koel, Ants 2021 IEEE International Conference on Consumer Electronics (ICCE) 2021 / 4 p. : ill <https://doi.org/10.1109/ICCE50685.2021.9427613> [Conference Proceedings at Scopus](#) [Article at Scopus](#) [Article at WOS](#)

Short-circuit protection circuits for silicon-carbide power transistors

Sadik, Diane-Perle; Colmenares, Juan; Tolstoy, Georg; **Rabkowski, Jacek** IEEE transactions on industrial electronics 2016 / p. 1995-2004 : ill <https://doi.org/10.1109/TIE.2015.2506628>

SiC schottky diode rectifier bridge represented as the diffusion-welded stack

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Sintering of silicon carbide obtained by combustion synthesis

Amirkhanyan, Narine; Kirakosyan, Hasmik; Zakaryan, Marieta; Zurnachyan, Alina; Rodriguez, Miguel Angel; Abovyan, L.; **Aydinyan, Sofiya** Ceramics international 2023 / p. 26129-26134 <https://doi.org/10.1016/j.ceramint.2023.04.233> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)